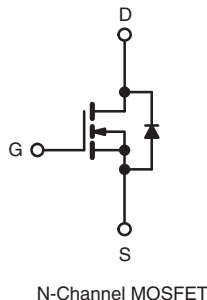
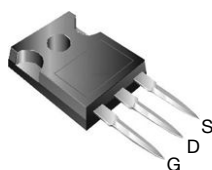


E Series Power MOSFET

PRODUCT SUMMARY

V_{DS} (V) at T_J max.	650	
$R_{DS(on)}$ max. at 25 °C (Ω)	$V_{GS} = 10$ V	0.064
Q_g max. (nC)	220	
Q_{gs} (nC)	36	
Q_{gd} (nC)	60	
Configuration	Single	

TO-247AC


FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- Low Figure-of-Merit (FOM) $R_{on} \times Q_g$
- Low Input Capacitance (C_{iss})
- Reduced Switching and Conduction Losses
- Ultra Low Gate Charge (Q_g)
- Avalanche Energy Rated (UIS)
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Switch Mode Power Supplies (SMPS)
- Power Factor Correction Power Supplies (PFC)
- Lighting
 - High-Intensity Discharge (HID)
 - Fluorescent Ballast Lighting
- Industrial
 - Welding
 - Induction Heating
 - Motor Drives
 - Battery Chargers
 - Renewable Energy
 - Solar (PV Inverters)

ORDERING INFORMATION

Package	TO-247AC
Lead (Pb)-free and Halogen-free	SiHG47N60E-GE3

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 20	
Gate-Source Voltage AC ($f > 1$ Hz)		30	
Continuous Drain Current ($T_J = 150$ °C)	I_D	47	A
		30	
Pulsed Drain Current ^a	I_{DM}	145	
Linear Derating Factor		3	W/°C
Single Pulse Avalanche Energy ^b	E_{AS}	1500	mJ
Maximum Power Dissipation	P_D	357	W
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to + 150	°C
Drain-Source Voltage Slope	dV/dt	37	V/ns
Reverse Diode dV/dt ^d		11	
Soldering Recommendations (Peak Temperature)	for 10 s	300°	°C

Notes

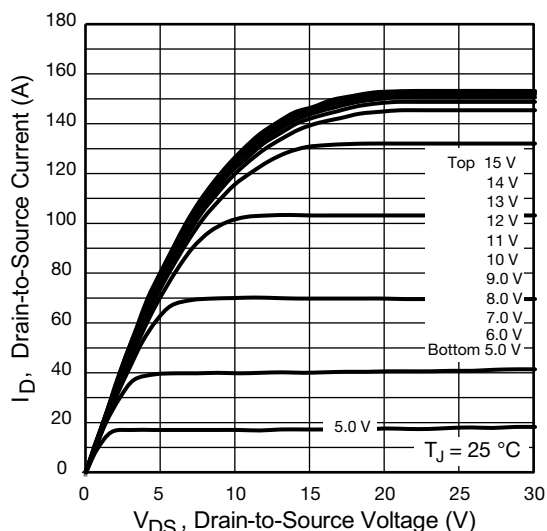
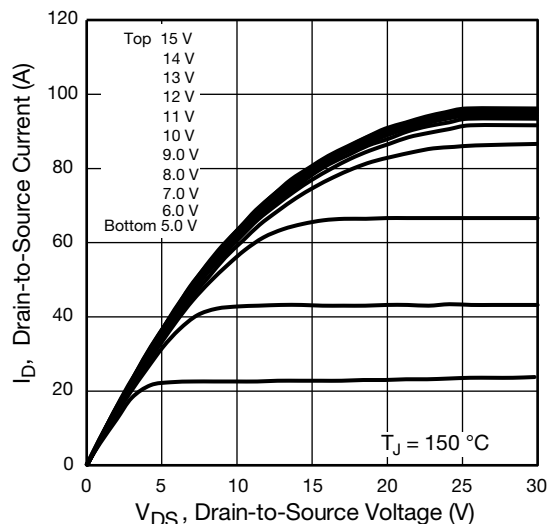
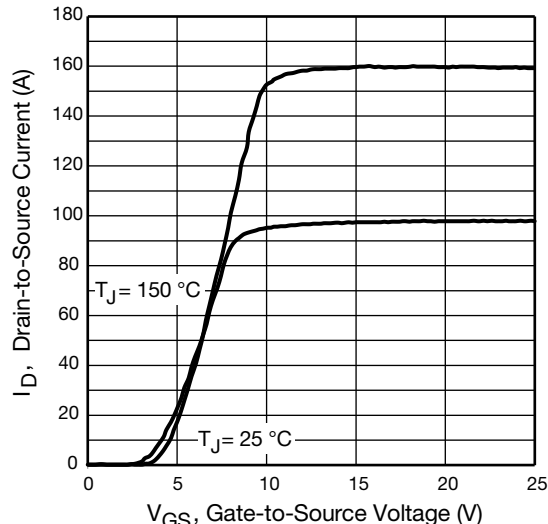
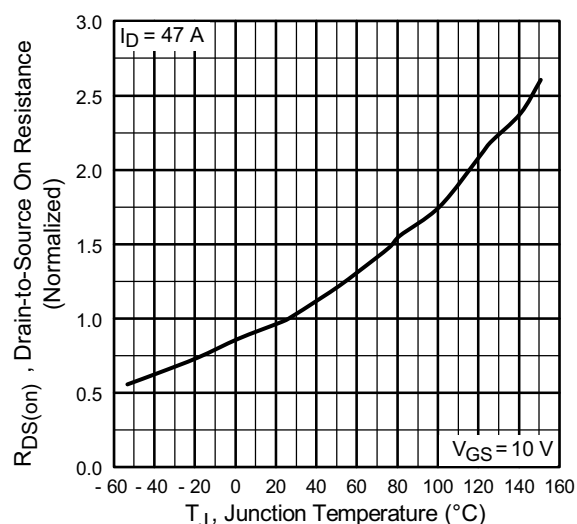
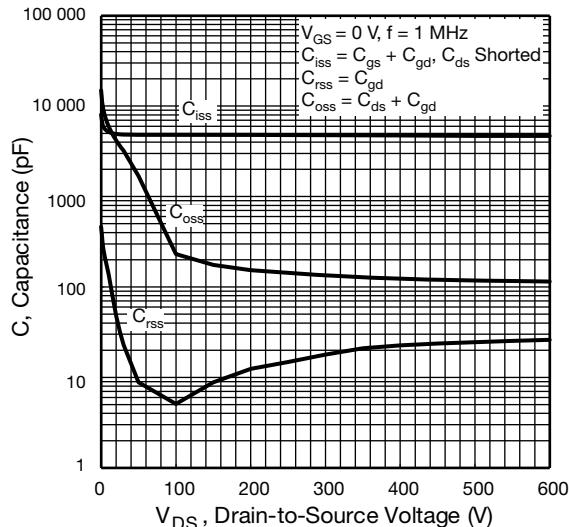
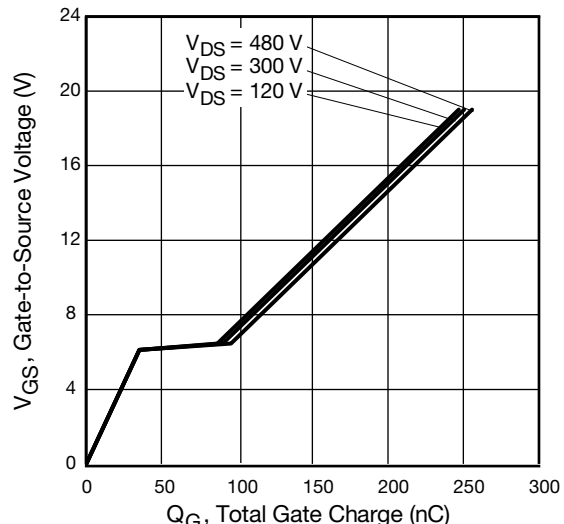
- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 50$ V, starting $T_J = 25$ °C, $L = 73.5$ mH, $R_g = 25$ Ω , $I_{AS} = 6.4$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 100$ A/ μ s, starting $T_J = 25$ °C.

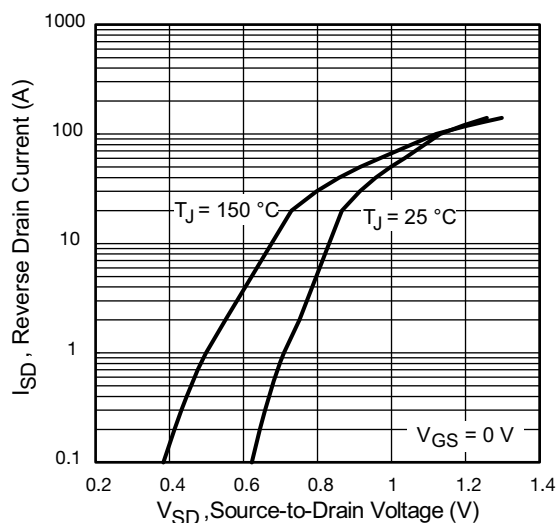
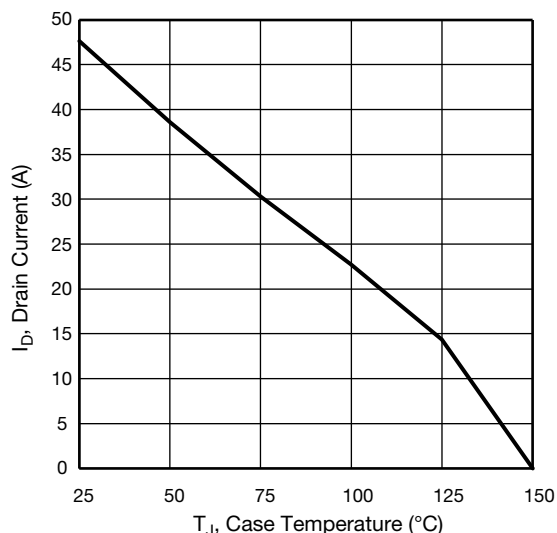
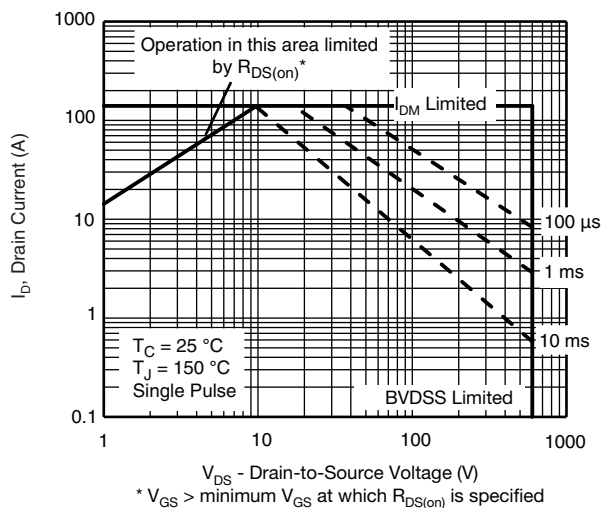
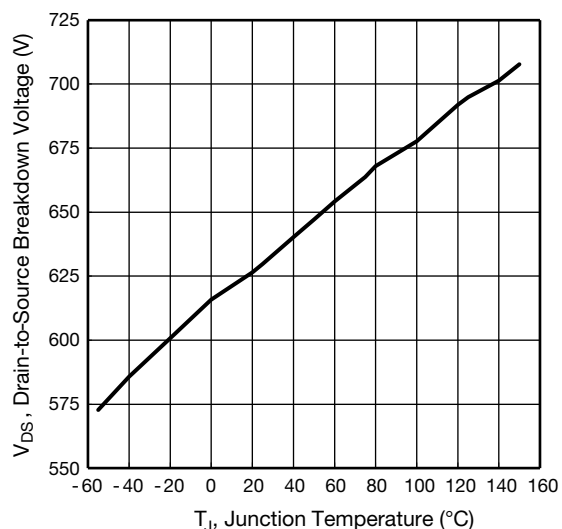
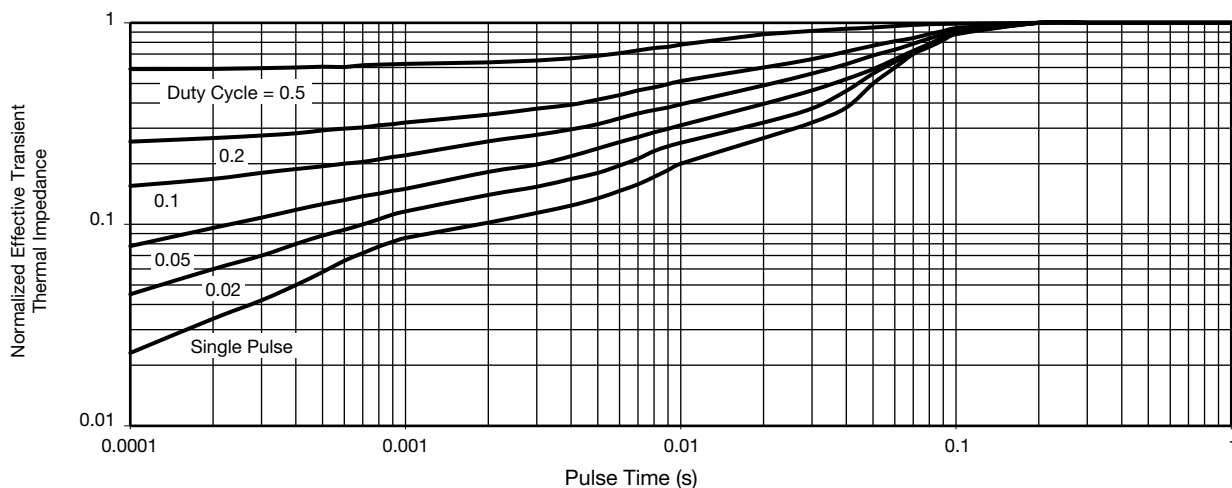
**THERMAL RESISTANCE RATINGS**

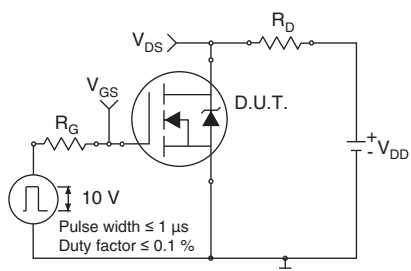
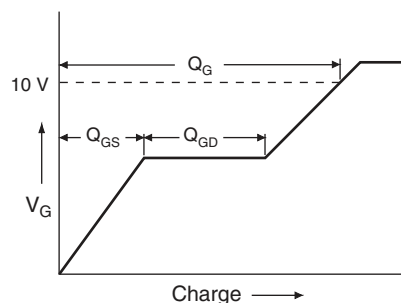
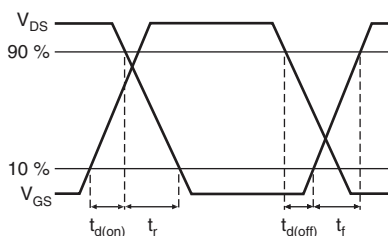
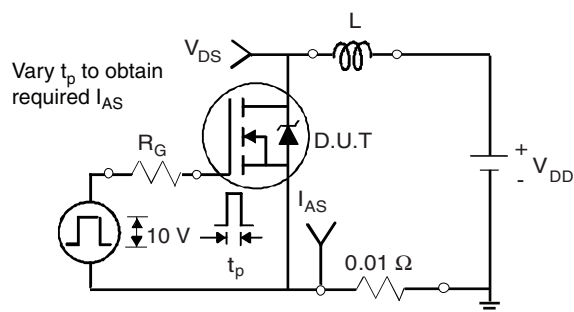
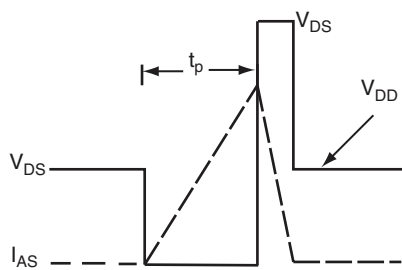
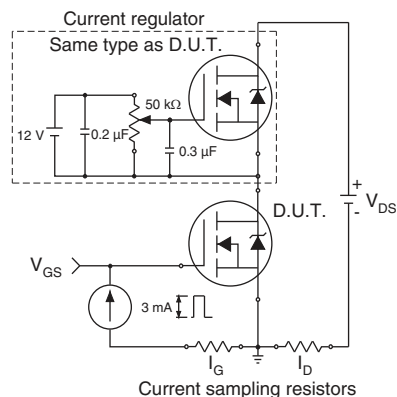
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.33	

SPECIFICATIONS ($T_J = 25\text{ °C}$, unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA		600	-	-	V
V _{DS} Temperature Coefficient	ΔV _{DS} /T _J	Reference to 25 °C, I _D = 250 μA		-	0.66	-	V/°C
Gate-Source Threshold Voltage (N)	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA		2	-	4	V
Gate-Source Leakage	I _{GSS}	V _{GS} = ± 20 V		-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V		-	-	1	μA
		V _{DS} = 480 V, V _{GS} = 0 V, T _J = 150 °C		-	-	10	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 24 A	-	0.053	0.064	Ω
Forward Transconductance	g _{fs}	V _{DS} = 8 V, I _D = 3 A		-	6.8	-	S
Dynamic							
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 100 V, f = 1 MHz		-	4810	-	pF
Output Capacitance	C _{oss}			-	230	-	
Reverse Transfer Capacitance	C _{rss}			-	5	-	
Total Gate Charge	Q _g	V _{GS} = 10 V	I _D = 47 A, V _{DS} = 480 V	-	147	220	nC
Gate-Source Charge	Q _{gs}			-	36	-	
Gate-Drain Charge	Q _{gd}			-	60	-	
Turn-On Delay Time	t _{d(on)}	V _{DD} = 480 V, I _D = 47 A, V _{GS} = 10 V, R _g = 4.4 Ω		-	24	50	ns
Rise Time	t _r			-	11	25	
Turn-Off Delay Time	t _{d(off)}			-	94	140	
Fall Time	t _f			-	13	26	
Gate Input Resistance	R _g	f = 1 MHz, open drain		-	0.65	-	Ω
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I _S	MOSFET symbol showing the integral reverse p - n junction diode 		-	-	47	A
Pulsed Diode Forward Current	I _{SM}			-	-	140	
Diode Forward Voltage	V _{SD}	T _J = 25 °C, I _S = 47 A, V _{GS} = 0 V		-	-	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C, I _F = I _S = 47 A, dI/dt = 100 A/μs, V _R = 25 V		-	696	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}			-	16	-	μC
Reverse Recovery Current	I _{RRM}			-	39	-	A

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Fig. 1 - Typical Output Characteristics, $T_C = 25^\circ\text{C}$

Fig. 2 - Typical Output Characteristics, $T_C = 150^\circ\text{C}$

Fig. 3 - Typical Transfer Characteristics

Fig. 4 - Normalized On-Resistance vs. Temperature

Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage


Fig. 7 - Typical Source-Drain Diode Forward Voltage

Fig. 9 - Maximum Drain Current vs. Case Temperature

Fig. 8 - Maximum Safe Operating Area

Fig. 10 - Temperature vs. Drain-to-Source Voltage

Fig. 11 - Normalized Thermal Transient Impedance, Junction-to-Case


Fig. 12 - Switching Time Test Circuit

Fig. 16 - Basic Gate Charge Waveform

Fig. 13 - Switching Time Waveforms

Fig. 14 - Unclamped Inductive Test Circuit

Fig. 15 - Unclamped Inductive Waveforms

Fig. 17 - Gate Charge Test Circuit



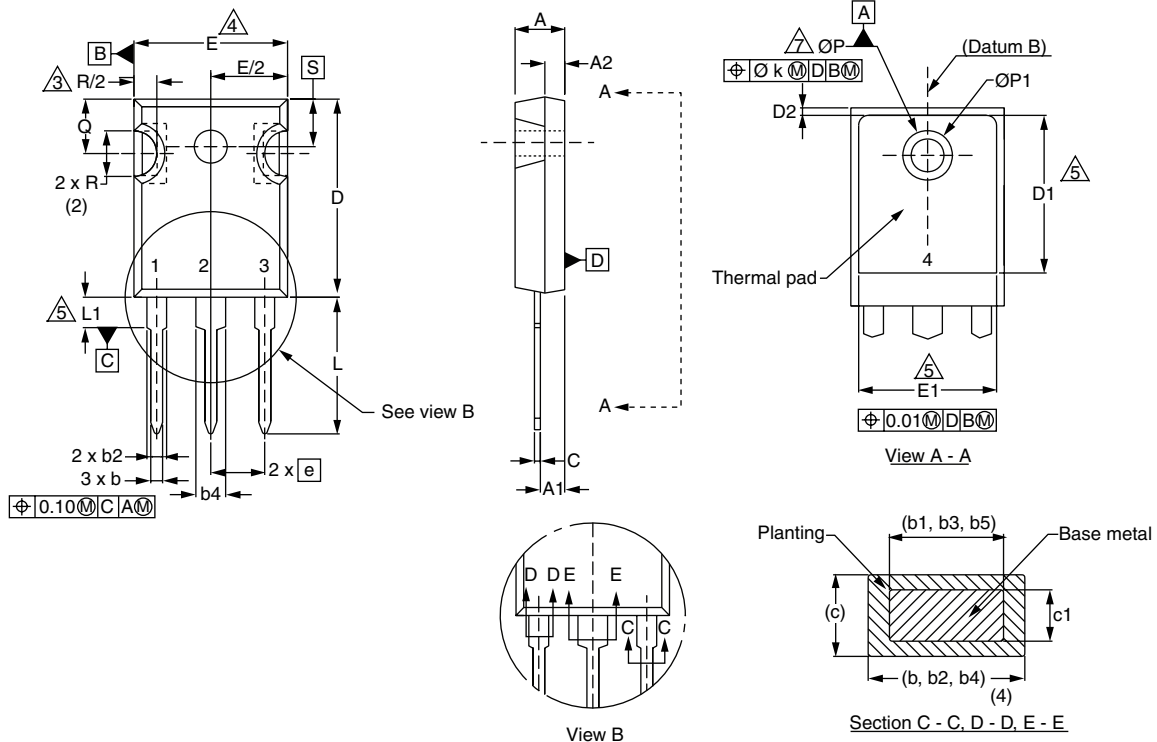
Note

a. $V_{GS} = 5\text{ V}$ for logic level devices

Fig. 18 - For N-Channel

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TO-247AC (HIGH VOLTAGE)



DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	4.65	5.31	0.183	0.209
A1	2.21	2.59	0.087	0.102
A2	1.50	2.49	0.059	0.098
b	0.99	1.40	0.039	0.055
b1	0.99	1.35	0.039	0.053
b2	1.65	2.39	0.065	0.094
b3	1.65	2.37	0.065	0.093
b4	2.59	3.43	0.102	0.135
b5	2.59	3.38	0.102	0.133
c	0.38	0.86	0.015	0.034
c1	0.38	0.76	0.015	0.030
D	19.71	20.70	0.776	0.815
D1	13.08	-	0.515	-

DIM.	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
D2	0.51	1.30	0.020	0.051
E	15.29	15.87	0.602	0.625
E1	13.72	-	0.540	-
e	5.46 BSC		0.215 BSC	
Ø k	0.254		0.010	
L	14.20	16.10	0.559	0.634
L1	3.71	4.29	0.146	0.169
N	7.62 BSC		0.300 BSC	
Ø P	3.56	3.66	0.140	0.144
Ø P1	-	7.39	-	0.291
Q	5.31	5.69	0.209	0.224
R	4.52	5.49	0.178	0.216
S	5.51 BSC		0.217 BSC	

ECN: S-81920-Rev. A, 15-Sep-08
DWG: 5971

Notes

1. Dimensioning and tolerancing per ASME Y14.5M-1994.
2. Contour of slot optional.
3. Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body.
4. Thermal pad contour optional with dimensions D1 and E1.
5. Lead finish uncontrolled in L1.
6. Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154").
7. Outline conforms to JEDEC outline TO-247 with exception of dimension c.



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